

Supporting Information

**A High Responsivity, High Detectivity and High Response Speed MSM
UVB Photodetector based on SnO₂ Microwires**

Rongpeng Fu^{†a}, Xue Jiang^{†a}, Yuefei Wang^a, Danyang Xia^a, Bingsheng Li^{a,*}, Jiangang Ma^a, Haiyang Xu^a,

Aidong Shen^b, Yichun Liu^a

^aKey Laboratory of UV Light Emitting Materials and Technology Under Ministry of Education, Northeast

Normal University, Changchun 130024, P. R. China

^bDepartment of Electrical Engineering, The City College of New York, New York 10031, USA

Corresponding Authors

*E-mail: libs@nenu.edu.cn

[†]These authors contributed equally to this work.

S1 Comparisons between the fabricated SnO₂ MWs in this work and other previous reports

Tab. S1 shows the comparison of the device performance parameters for this work and some previous reports. Similar with the junction type devices, the SnO₂ MW in this work also shows relatively low dark current and response time, which is attributed to the relatively high crystal quality and small amount of oxygen vacancies existed inside the material. While different with the reported junction type devices, SnO₂ MW in this work shows higher responsivity and specific detectivity, which can be attributed to the excellent performance of carrier generation and transportation.

Tab. S1 Comparisons between the fabricated SnO₂ MWs in this work and other previous reports.

Material	Bias V	Dark current A	Responsivity A·W ⁻¹	Detectivity Jones	Response time s	Ref.
SnO ₂ /CsPbBr ₃	3	1.0×10 ⁻¹⁰	2.0	1.2×10 ¹³	1.94×10 ⁻³	1
SnO ₂	3	1.0×10 ⁻⁹	--	--	1.0	2
β-Ga ₂ O ₃ /SnO ₂	2	2.0×10 ⁻⁹	--	--	28.0	3
SnO ₂ /p-GaN	-3	1.6×10 ⁻⁸	1.45	1.31×10 ¹³	0.51	4
PEDOT:PSS/SnO ₂	-10	1.1×10 ⁻⁴	1.8×10 ⁻³	--	--	5
SnO ₂ /p-InGaN	0	--	0.1	3.5×10 ¹² (-0.1 V)	0.5	6
SnO ₂ (322 nm, 0.25 μW/cm ²)	10	3.69×10 ⁻⁹	1.353×10 ³	5.4×10 ¹⁴	< 8.0×10 ⁻²	This work

S2 The absorption spectrum of single SnO₂ MW

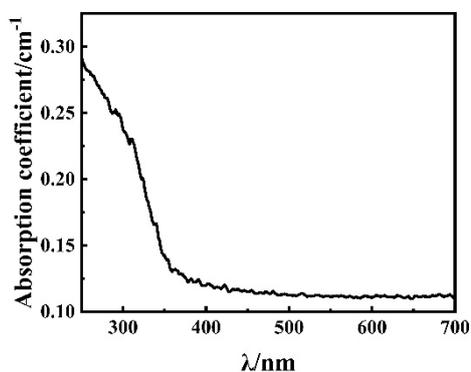


Fig. S1 Absorption spectrum of single SnO₂ MW

S3 The element content and distribution of SnO₂ MWs

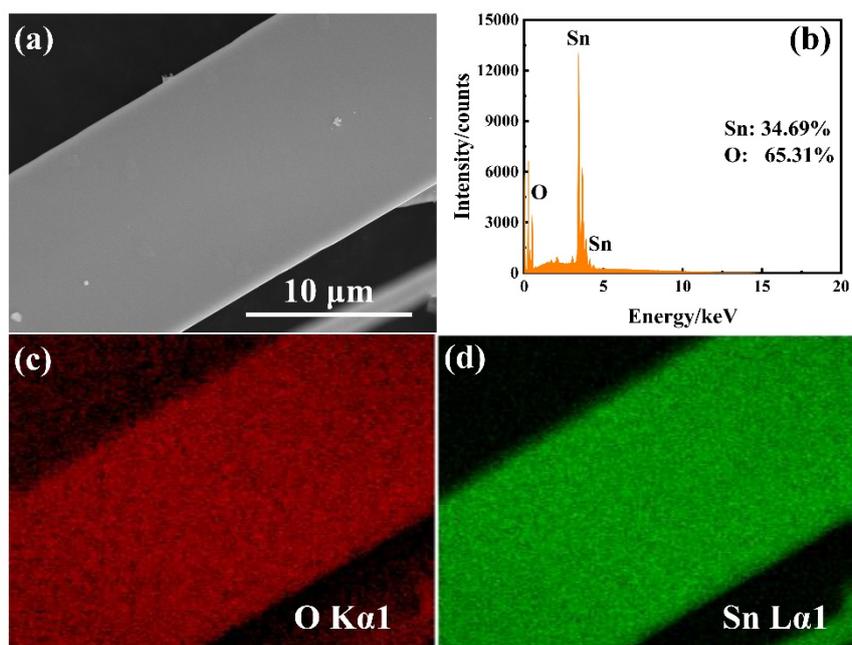


Fig. S2 (a) The SEM image of SnO₂ MWs; (b) the measured distribution spectrum of elements; (c - d) the measured element mappings of O and Sn elements in SnO₂ MWs.

References

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